

Schottky Barrier Diode

Features

1. High reliability
2. Low reverse current and low forward voltage



Applications

Low current rectification and high speed switching

Construction

Silicon epitaxial planar

Absolute Maximum Ratings

$T_j=25^{\circ}\text{C}$

Parameter	Test Conditions	Type	Symbol	Value	Unit
Repetitive peak reverse voltage		LL60	V_{RRM}	40	V
		LL60P	V_{RRM}	45	V
Peak forward surge current	$t_p \leq 1 \text{ s}$	LL60	I_{FSM}	150	mA
		LL60P	I_{FSM}	500	mA
Forward continuous current	$T_a=25^{\circ}\text{C}$	LL60	I_F	30	mA
		LL60P	I_F	50	mA
Storage temperature range			T_{stg}	-65~+125	$^{\circ}\text{C}$

Stresses exceeding maximum ratings may damage the device. Maximum ratings are stress ratings only. Functional operation above the recommended operating conditions is not implied. Extended exposure to stresses above the recommended operating conditions may affect device reliability.

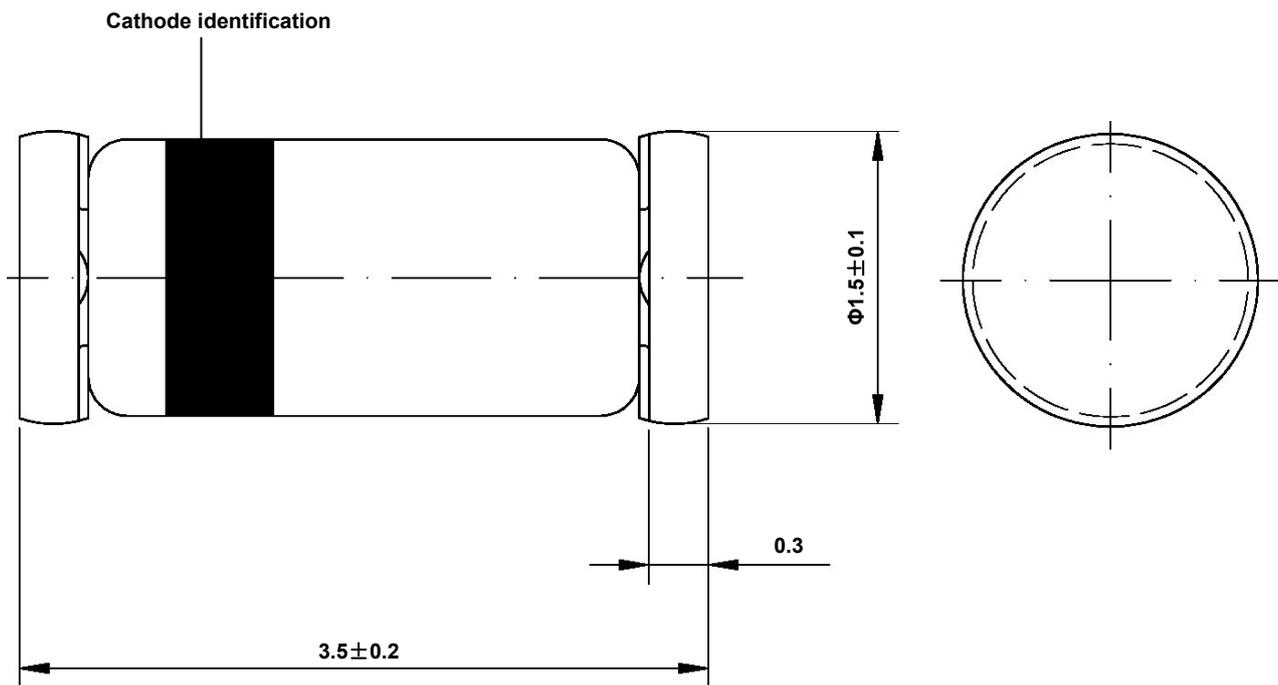
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Electrical Characteristics

$T_j=25^{\circ}\text{C}$

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F=1\text{mA}$	LL60	V_F		0.32	0.5	V
		LL60P	V_F		0.24	0.5	V
	$I_F=30\text{mA}$	LL60	V_F		0.65	1.0	V
	$I_F=200\text{mA}$	LL60P	V_F		0.65	1.0	V
Reverse current	$V_R=15\text{V}$	LL60	I_R		0.1	0.5	μA
		LL60P	I_R		0.5	1.0	μA
Junction capacitance	$V_R=1\text{V}, f=1\text{MHz}$	LL60	C_J		2.0		pF
	$V_R=10\text{V}, f=1\text{MHz}$	LL60P	C_J		6.0		pF
Reverse recovery time	$I_F=I_R=1\text{mA } I_{tr}=1\text{mA } R_C=100\Omega$		t_{rr}			1.0	ns

Dimensions in mm



Glass Case
 Mini Melf / SOD-80
 JEDEC DO-213 AA

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